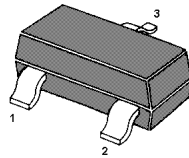


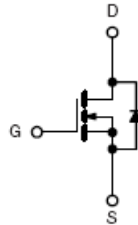
## N-Channel 20-V(D-S) MOSFET

SOT-23



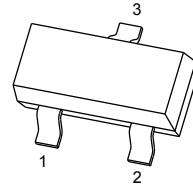
MARKING : S12

Equivalent Circuit



SOT-23

1. GATE
2. SOURCE
3. DRAIN



| $V_{(BR)DSS}$ | $R_{DS(on)Typ}$    | $I_D$ |
|---------------|--------------------|-------|
| 20 V          | 31m $\Omega$ @4.5V | 5A    |
|               | 35m $\Omega$ @2.5V |       |
|               |                    |       |

Maximum ratings ( $T_a=25^{\circ}\text{C}$  unless otherwise noted)

| Parameter                                        | Symbol          | Value      | Unit                 |
|--------------------------------------------------|-----------------|------------|----------------------|
| Drain-Source Voltage                             | $V_{DS}$        | 20         | V                    |
| Gate-Source Voltage                              | $V_{GS}$        | $\pm 10$   |                      |
| Continuous Drain Current $t=5s$                  | $I_D$           | 5          | A                    |
| Pulsed Drain Current                             | $I_{DM}$        | 20         |                      |
| Continuous Source-Drain Diode Current            | $I_S$           | 1.04       |                      |
| Maximum Power Dissipation $t=5s$                 | $P_D$           | 0.35       | W                    |
| Thermal Resistance from Junction to Ambient      | $R_{\theta JA}$ | 357        | $^{\circ}\text{C/W}$ |
| Operation Junction and Storage Temperature Range | $T_J, T_{stg}$  | -50 ~ +150 | $^{\circ}\text{C}$   |

## MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^{\circ}\text{C}$  unless otherwise specified

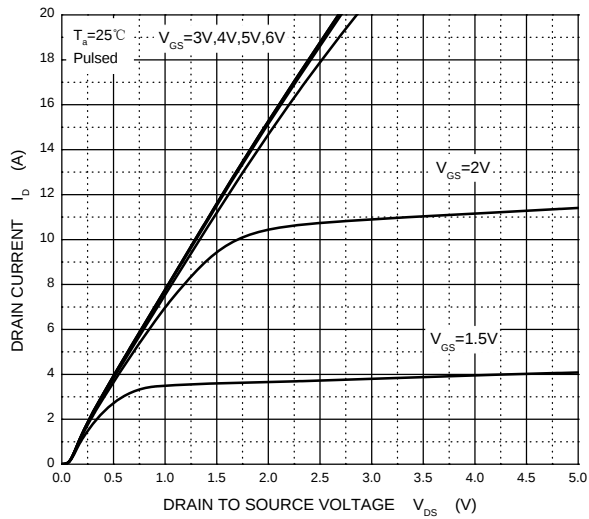
| Parameter                                     | Symbol                | Test Condition                                                                                            | Min  | Typ   | Max   | Unit |
|-----------------------------------------------|-----------------------|-----------------------------------------------------------------------------------------------------------|------|-------|-------|------|
| Static                                        |                       |                                                                                                           |      |       |       |      |
| Drain-source breakdown voltage                | V <sub>(BR) DSS</sub> | V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA                                                               | 20   |       |       | V    |
| Gate-source leakage                           | I <sub>GSS</sub>      | V <sub>DS</sub> =0V, V <sub>GS</sub> =±8V                                                                 |      |       | ±100  | nA   |
| Zero gate voltage drain current               | I <sub>DSS</sub>      | V <sub>DS</sub> =20V, V <sub>GS</sub> =0V                                                                 |      |       | 1.0   | μA   |
| Gate-source threshold voltage                 | V <sub>GS(th)</sub>   | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA                                                  | 0.45 | 0.7   | 1.0   | V    |
| Drain-source on-state resistance <sup>a</sup> | R <sub>DS(on)</sub>   | V <sub>GS</sub> =4.5V, I <sub>D</sub> =5.0A                                                               |      | 0.031 | 0.032 | Ω    |
|                                               |                       | V <sub>GS</sub> =2.5V, I <sub>D</sub> =4A                                                                 |      | 0.035 | 0.042 |      |
|                                               |                       |                                                                                                           |      |       |       |      |
| Forward tranconductance <sup>a</sup>          | g <sub>fs</sub>       | V <sub>DS</sub> =10V, I <sub>D</sub> =5.0A                                                                |      | 6     |       | S    |
| Dynamic <sup>b</sup>                          |                       |                                                                                                           |      |       |       |      |
| Input capacitance                             | C <sub>iss</sub>      | V <sub>DS</sub> =10V,V <sub>GS</sub> =0V,f =1MHz                                                          |      | 865   |       | pF   |
| Output capacitance                            | C <sub>oss</sub>      |                                                                                                           |      | 105   |       |      |
| Reverse transfer capacitance                  | C <sub>rss</sub>      |                                                                                                           |      | 55    |       |      |
| Gate resistance                               | R <sub>g</sub>        | f =1MHz                                                                                                   | 0.5  |       | 4.8   | Ω    |
| Turn-on delay Time                            | t <sub>d(on)</sub>    | V <sub>GEN</sub> =5V,V <sub>DD</sub> =10V,<br>I <sub>D</sub> =4A,R <sub>G</sub> =1Ω, R <sub>L</sub> =2.2Ω |      |       | 10    | ns   |
| Rise time                                     | t <sub>r</sub>        |                                                                                                           |      |       | 20    |      |
| Turn-off Delay time                           | t <sub>d(off)</sub>   |                                                                                                           |      |       | 32    |      |
| Fall yime                                     | t <sub>f</sub>        |                                                                                                           |      |       | 12    |      |
| Drain-source body diode characteristics       |                       |                                                                                                           |      |       |       |      |
| Forward diode voltage                         | V <sub>SD</sub>       | V <sub>GS</sub> =0V,I <sub>S</sub> =4A                                                                    |      | 0.75  | 1.2   | V    |

### Notes :

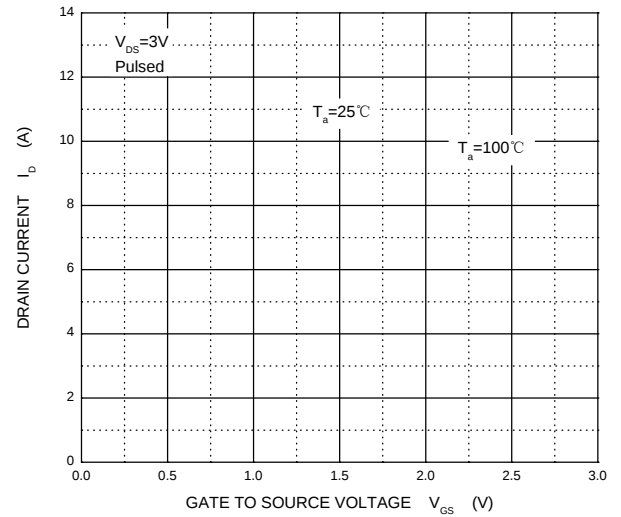
- Pulse Test : pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- These parameters have no way to verify.

## Typical Characteristics

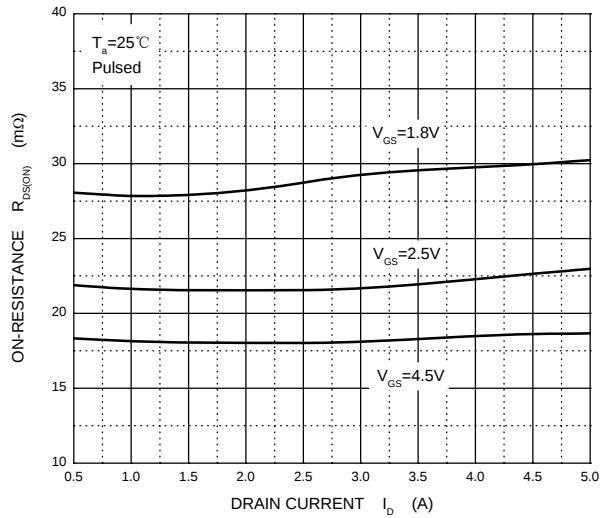
Output Characteristics



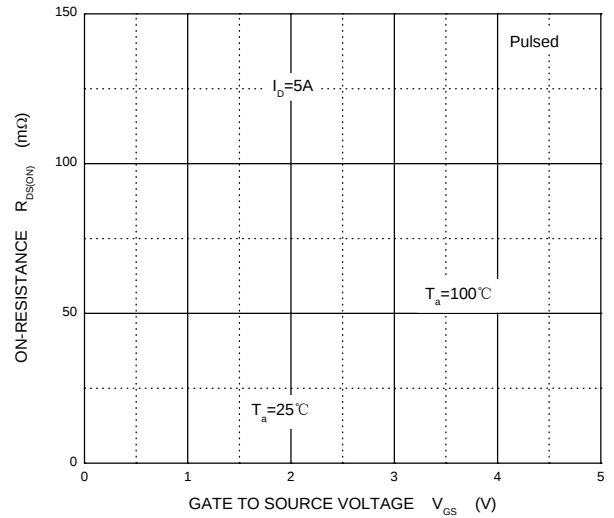
Transfer Characteristics



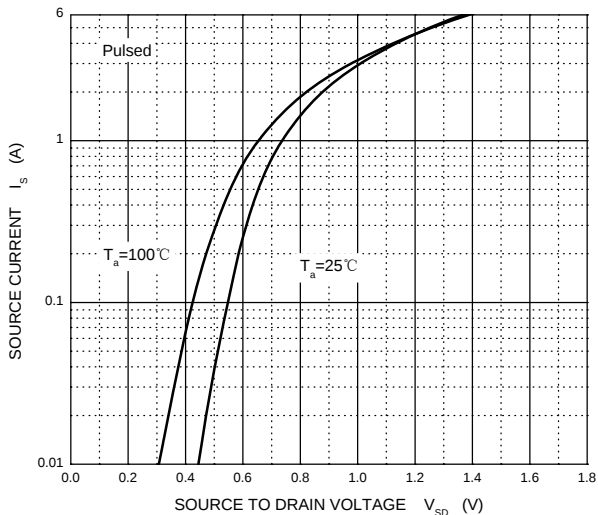
$R_{DS(ON)}$  —  $I_D$



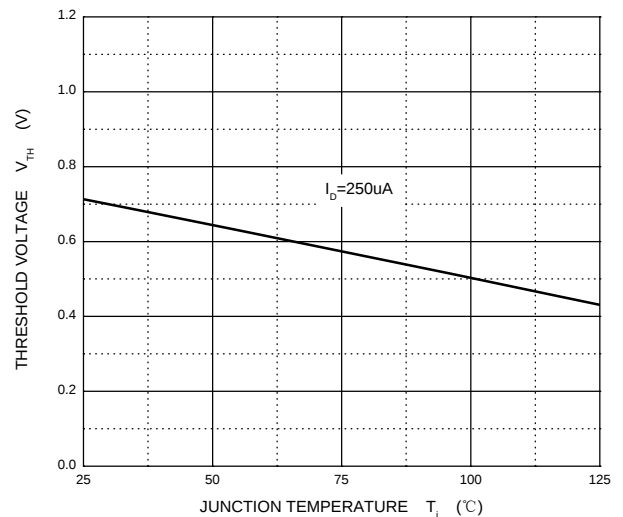
$R_{DS(ON)}$  —  $V_{GS}$



$I_S$  —  $V_{SD}$

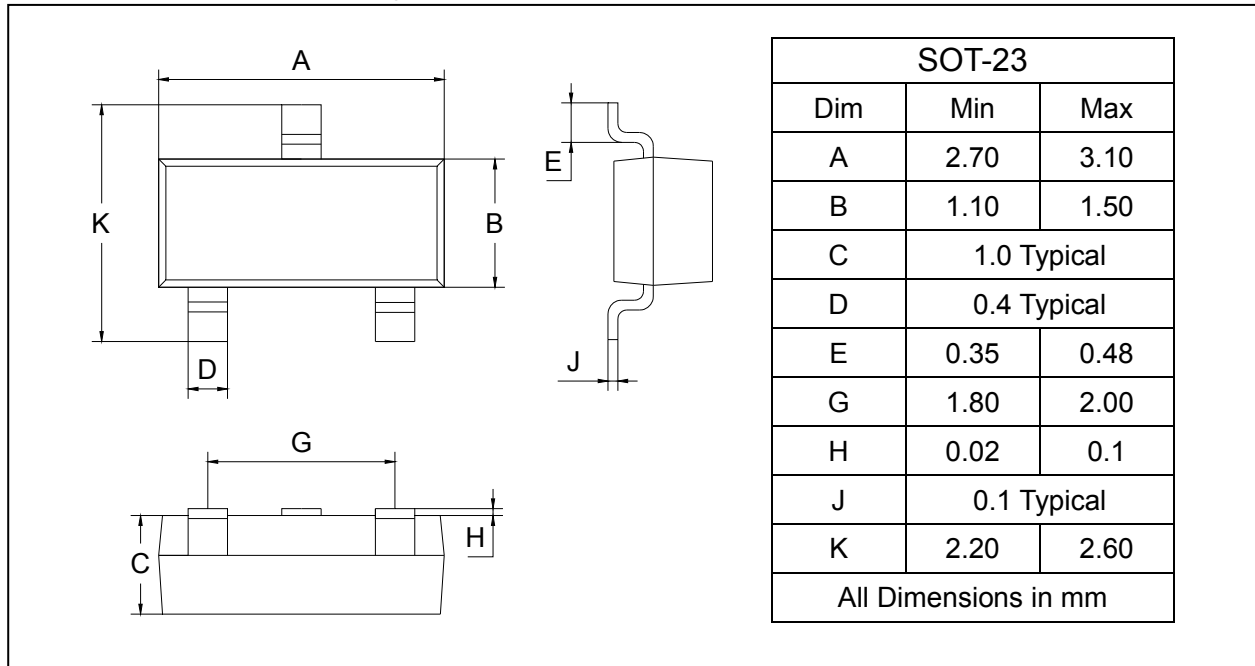


Threshold Voltage

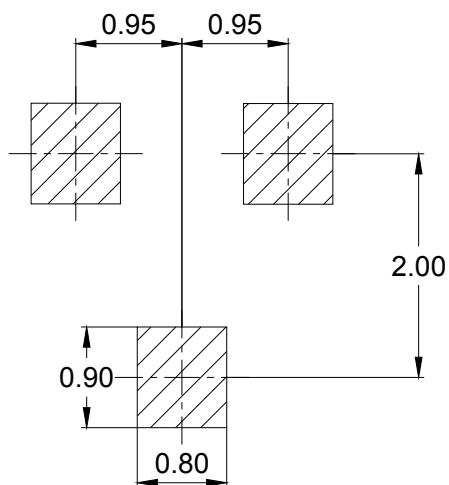


Plastic surface mounted package

SOT-23



## SOLDERING FOOTPRINT



Unit : mm